

**S I 2301** P-Channel 1.25-W, 2.5-V MOSFET

SI2301是二三级管的一种,属于场效应管。

# 主要参数:

晶体管类型 : P沟道MOSFET

最大功耗PD : 1.25W

栅极门限电压VGS : 2.5V (典型值) 漏源电压VDS : -20V (极限值)

漏极电流ID: - 2.3A

通态电阻RDS(on): 0.145ohm(典型值)

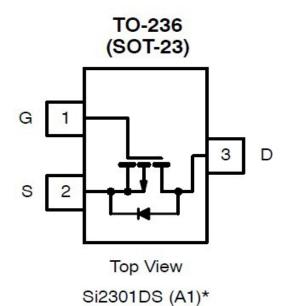
栅极漏电流IGSS: ± 100nA

结温:55 to+150 封装:SOT-23(TO-236)

# 替代型号:

WT-2301 WTC2301 SMG2301 CES2301 KI2301BDS

# PIN 配置:

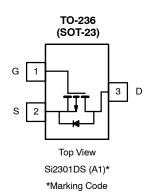


\*Marking Code



# P-Channel 1.25-W, 2.5-V MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$V_{DS}(V)$ $r_{DS(on)}(\Omega)$		
-20	0.130 @ V <sub>GS</sub> = -4.5 V	-2.3	
	0.190 @ V <sub>GS</sub> = -2.5 V	-1.9	



Ordering Information: Si2301DS-T1

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	-20	v		
Gate-Source Voltage		V <sub>GS</sub>	±8			
0 // D / 0 / 7 /	T <sub>A</sub> = 25°C		-2.3			
Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>b</sup>	T <sub>A</sub> = 70°C	l <sub>D</sub>	-1.5			
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	-10	^		
Continuous Source Current (Diode Conduction) <sup>b</sup>		Is	-1.6			
D. Division b	T <sub>A</sub> = 25°C		1.25	.,,		
Power Dissipation <sup>b</sup>	T <sub>A</sub> = 70°C	P <sub>D</sub>	0.8	w		
Operating Junction and Storage Temperature Range	<u>'</u>	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient <sup>b</sup>	_	100	
Maximum Junction-to-Ambient <sup>c</sup>	R <sub>thJA</sub>	166	°C/W

#### Notes

- Pulse width limited by maximum junction temperature. Surface Mounted on FR4 Board,  $t \le 5$  sec. Surface Mounted on FR4 Board.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm

# Si2301DS SI2301 P沟道MOSFET 1.25W 2.5V

# Vishay Siliconix



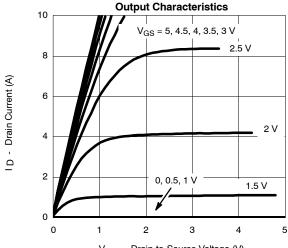
Parameter		Test Conditions	Limits			
	Symbol		Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu A$	-20			
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-0.45			V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±8 V			± 100	nA
Zero Gate Voltage Drain Current		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
	IDSS	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-10	
On-State Drain Current <sup>a</sup>		$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-6			Α
	I <sub>D(on)</sub>	$V_{DS} \leq -5 \text{ V}, V_{GS} = -2.5 \text{ V}$	-3			
Drain-Source On-Resistance <sup>a</sup>		$V_{GS} = -4.5 \text{ V}, I_D = -2.8 \text{ A}$		0.105	0.130	Ω
	r <sub>DS(on)</sub>	$V_{GS} = -2.5$ V, $I_D = -2.0$ A		0.145	0.190	
Forward Transconductancea	9fs	$V_{DS} = -5 \text{ V}, I_{D} = -2.8 \text{ A}$		6.5		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -1.6 A, V <sub>GS</sub> = 0 V		-0.80	-1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	Qg			5.8	10	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}$ $I_D \cong -2.8 \text{ A}$		0.85		
Gate-Drain Charge	Q <sub>gd</sub>			1.70		
Input Capacitance	C <sub>iss</sub>			415		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = -6 V, $V_{GS}$ = 0, f = 1 MHz		223		
Reverse Transfer Capacitance	C <sub>rss</sub>			87		
Switching <sup>c</sup>			- 1			•
T O. T	t <sub>d(on)</sub>			13.0	25	
Turn-On Time	t <sub>r</sub>	$V_{DD} = -6 \text{ V, } R_L = 6 \Omega$		36.0	60	1
Turn-Off Time	t <sub>d(off)</sub>	$I_D \cong -1.0 \text{ A}, V_{GEN} = -4.5 \text{ V}$ $R_G = 6 \Omega$		42	70	ns
	t <sub>f</sub>	f		34	60	7

### Notes

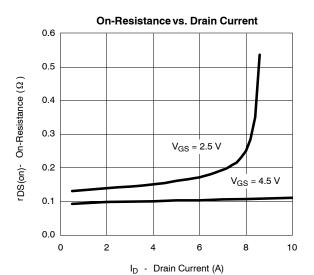
- a. Pulse test: PW ≤300 μs duty cycle ≤2%.
  b. For DESIGN AID ONLY, not subject to production testing.
  c. Switching time is essentially independent of operating temperature.



### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





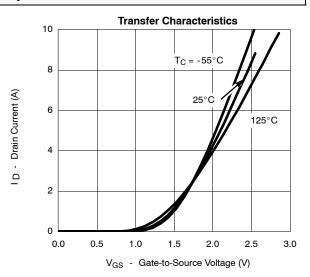


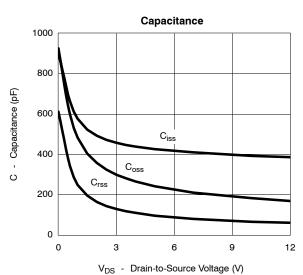
 $V_{DS} = 6 \text{ V}$  $I_{D} = 2.8 \text{ A}$ VGS - Gate-to-Source Voltage (V) 4 3 2 0 0 2 6

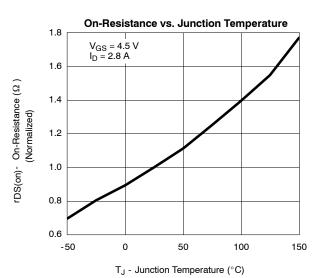
Q<sub>g</sub> - Total Gate Charge (nC)

5

**Gate Charge** 

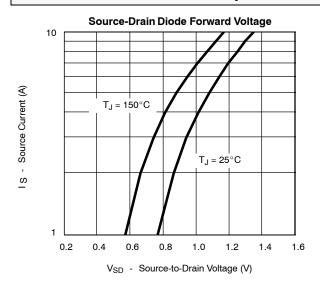


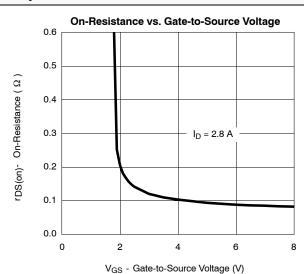


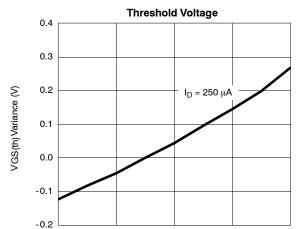




### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





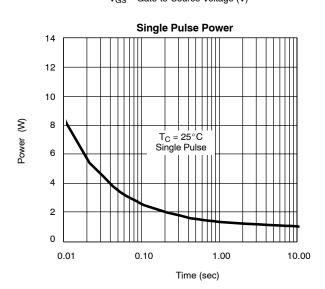


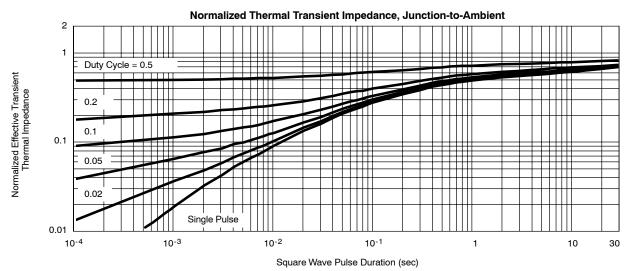
50

T<sub>J</sub> - Temperature (°C)

100

-50





150